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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, I²C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	DMA, I²S, POR, PWM, WDT
Number of I/O	87
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 17x12b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f302vbt6

3.7 Power management

3.7.1 Power supply schemes

- V_{SS}, V_{DD} = 2.0 to 3.6 V: external power supply for I/Os and the internal regulator. It is provided externally through V_{DD} pins.
- V_{SSA}, V_{DDA} = 2.0 to 3.6 V: external analog power supply for ADC, DAC, comparators operational amplifiers, reset blocks, RCs and PLL. The minimum voltage to be applied to V_{DDA} differs from one analog peripheral to another. *Table 3* provides the summary of the V_{DDA} ranges for analog peripherals. The V_{DDA} voltage level must be always greater or equal to the V_{DD} voltage level and must be provided first.
- V_{BAT} = 1.65 to 3.6 V: power supply for RTC, external clock 32 kHz oscillator and backup registers (through power switch) when V_{DD} is not present.

Table 3. External analog supply values for analog peripherals

Analog peripheral	Minimum V_{DDA} supply	Maximum V_{DDA} supply
ADC / COMP	2.0 V	3.6 V
DAC / OPAMP	2.4 V	3.6V

3.7.2 Power supply supervision

The device has an integrated power-on reset (POR) and power-down reset (PDR) circuits. They are always active, and ensure proper operation above a threshold of 2 V. The device remains in reset mode when the monitored supply voltage is below a specified threshold, $V_{POR/PDR}$, without the need for an external reset circuit.

- The POR monitors only the V_{DD} supply voltage. During the startup phase it is required that V_{DDA} should arrive first and be greater than or equal to V_{DD}.
- The PDR monitors both the V_{DD} and V_{DDA} supply voltages, however the V_{DDA} power supply supervisor can be disabled (by programming a dedicated Option bit) to reduce the power consumption if the application design ensures that V_{DDA} is higher than or equal to V_{DD}.

The device features an embedded programmable voltage detector (PVD) that monitors the V_{DD} power supply and compares it to the V_{PVD} threshold. An interrupt can be generated when V_{DD} drops below the V_{PVD} threshold and/or when V_{DD} is higher than the V_{PVD} threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

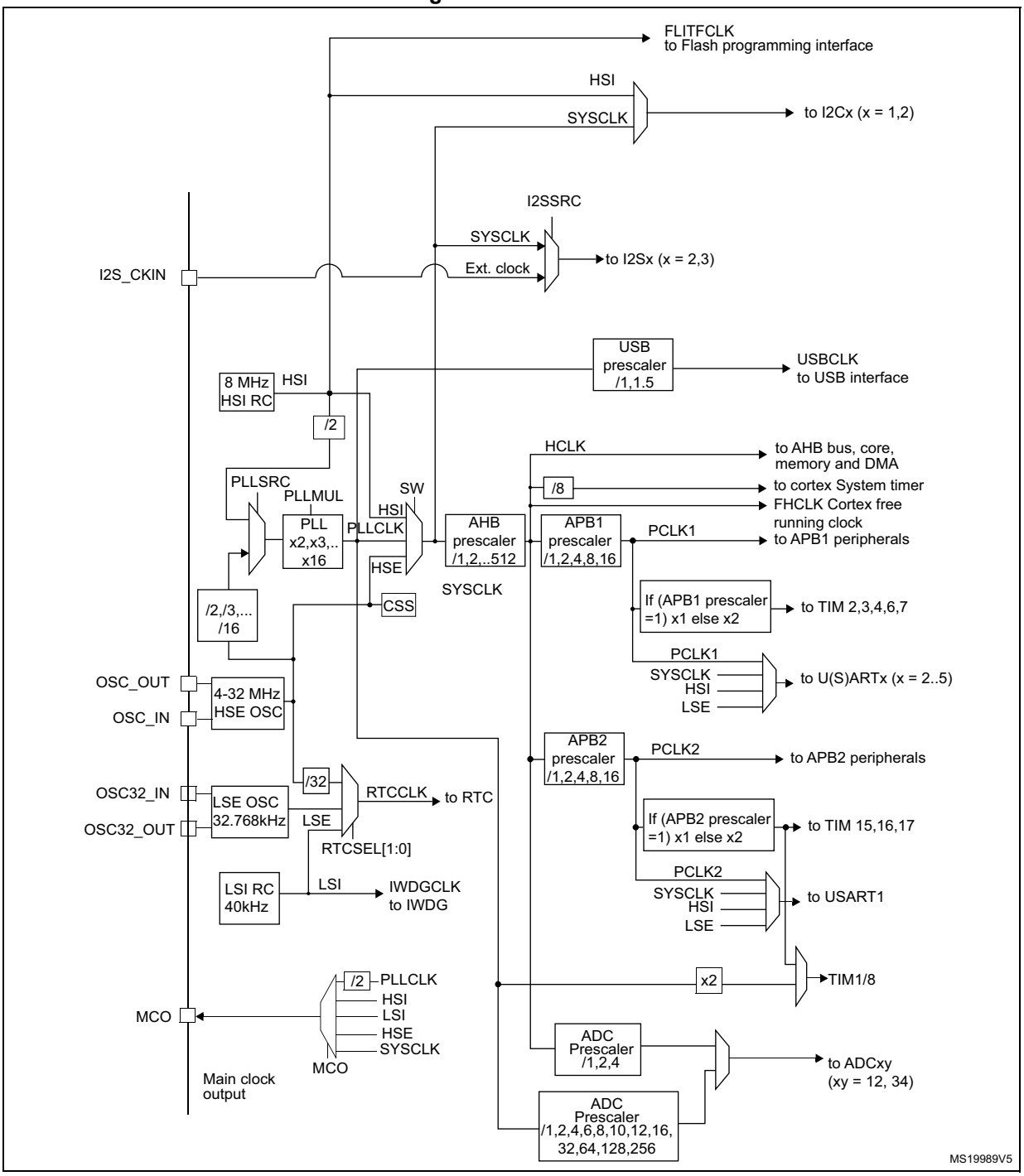
3.7.3 Voltage regulator

The regulator has three operation modes: main (MR), low-power (LPR), and power-down.

- The MR mode is used in the nominal regulation mode (Run)
- The LPR mode is used in Stop mode.
- The power-down mode is used in Standby mode: the regulator output is in high impedance, and the kernel circuitry is powered down thus inducing zero consumption.

The voltage regulator is always enabled after reset. It is disabled in Standby mode.

Figure 2. Clock tree



3.13.3 V_{BAT} battery voltage monitoring

This embedded hardware feature allows the application to measure the V_{BAT} battery voltage using the internal ADC channel ADC1_IN17. As the V_{BAT} voltage may be higher than V_{DDA}, and thus outside the ADC input range, the V_{BAT} pin is internally connected to a bridge divider by 2. As a consequence, the converted digital value is half the V_{BAT} voltage.

3.13.4 OPAMP reference voltage (VREFOPAMP)

Every OPAMP reference voltage can be measured using a corresponding ADC internal channel: VREFOPAMP1 connected to ADC1 channel 15, VREFOPAMP2 connected to ADC2 channel 17.

3.14 Digital-to-analog converter (DAC)

A single 12-bit buffered DAC channel can be used to convert digital signals into analog voltage signal outputs. The chosen design structure is composed of integrated resistor strings and an amplifier in inverting configuration.

This digital interface supports the following features:

- One DAC output channel
- 8-bit or 10-bit monotonic output
- Left or right data alignment in 12-bit mode
- Noise-wave generation
- Triangular-wave generation
- DMA capability
- External triggers for conversion

3.15 Operational amplifier (OPAMP)

The STM32F302xB/STM32F302xC embeds two operational amplifiers with external or internal follower routing and PGA capability (or even amplifier and filter capability with external components). When an operational amplifier is selected, an external ADC channel is used to enable output measurement.

The operational amplifier features:

- 8.2 MHz bandwidth
- 0.5 mA output capability
- Rail-to-rail input/output
- In PGA mode, the gain can be programmed to be 2, 4, 8 or 16.

3.16 Fast comparators (COMP)

The STM32F302xB/STM32F302xC devices embed four fast rail-to-rail comparators with programmable reference voltage (internal or external), hysteresis and speed (low speed for low-power) and with selectable output polarity.

Figure 5. STM32F302xB/STM32F302xC LQFP64 pinout

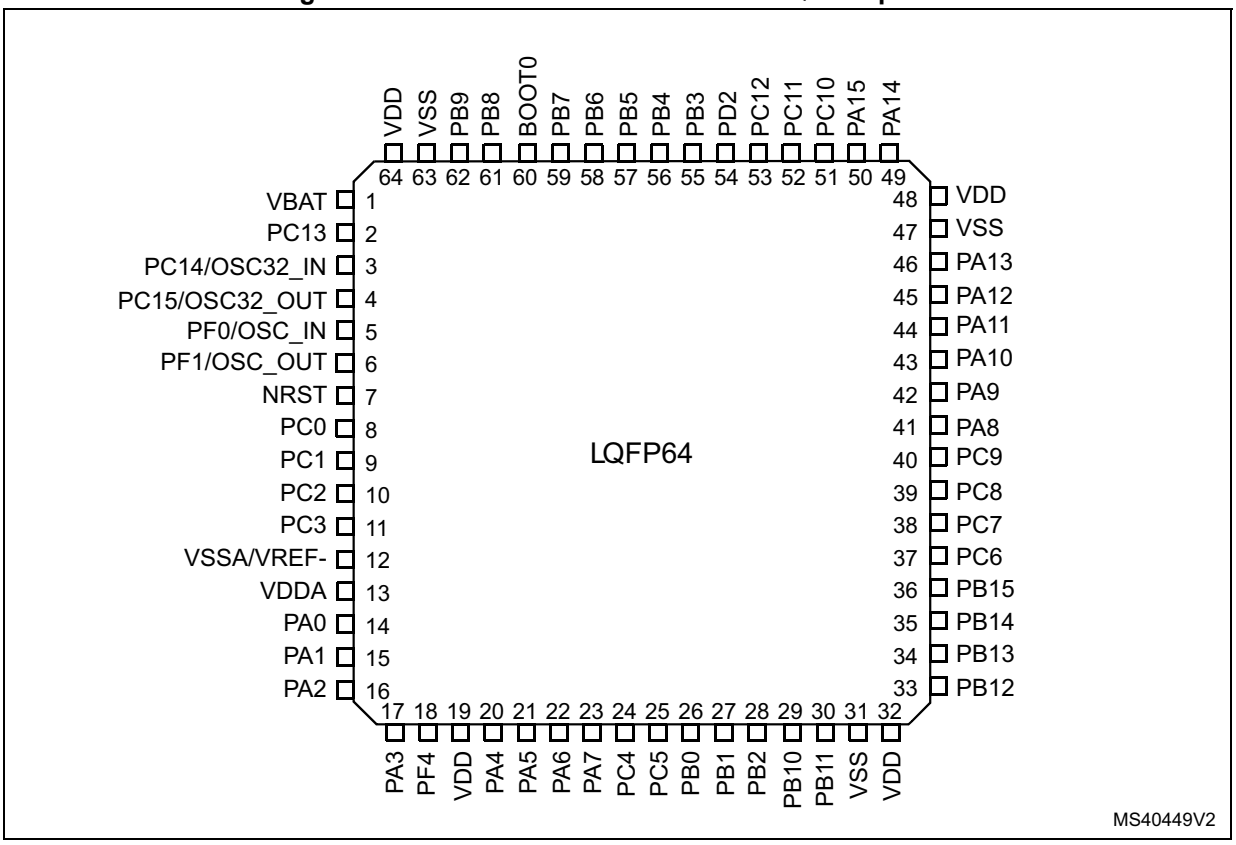


Table 13. STM32F302xB/STM32F302xC pin definitions (continued)

Pin number				Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
WLCSP100	LQFP100	LQFP64	LQFP48					Alternate functions	Additional functions
C3	82	-	-	PD1	I/O	FT	(1)	CAN_TX, EVENTOUT	-
A4	83	54	-	PD2	I/O	FT	(1)	UART5_RX, TIM3_ETR, EVENTOUT	-
B4	84	-	-	PD3	I/O	FT	(1)	USART2_CTS, TIM2_CH1_ETR, EVENTOUT	-
C4	85	-	-	PD4	I/O	FT	(1)	USART2_RTS_DE, TIM2_CH2, EVENTOUT	-
-	86	-	-	PD5	I/O	FT	(1)	USART2_TX, EVENTOUT	-
-	87	-	-	PD6	I/O	FT	(1)	USART2_RX, TIM2_CH4, EVENTOUT	-
D4	88	-	-	PD7	I/O	FT	(1)	USART2_CK, TIM2_CH3, EVENTOUT	-
A5	89	55	39	PB3	I/O	FT	-	SPI3_SCK, I2S3_CK, SPI1_SCK, USART2_TX, TIM2_CH2, TIM3_ETR, TIM4_ETR, TSC_G5_IO1, JTDO-TRACESWO, EVENTOUT	-
B5	90	56	40	PB4	I/O	FT	-	SPI3_MISO, I2S3ext_SD, SPI1_MISO, USART2_RX, TIM3_CH1, TIM16_CH1, TIM17_BKIN, TSC_G5_IO2, NJTRST, EVENTOUT	-
A6	91	57	41	PB5	I/O	FT	-	SPI3_MOSI, SPI1_MOSI, I2S3_SD, I2C1_SMBA, USART2_CK, TIM16_BKIN, TIM3_CH2, TIM17_CH1, EVENTOUT	-
B6	92	58	42	PB6	I/O	FTf	-	I2C1_SCL, USART1_TX, TIM16_CH1N, TIM4_CH1, TSC_G5_IO3EVENTOUT	-
C5	93	59	43	PB7	I/O	FTf	-	I2C1_SDA, USART1_RX, TIM3_CH4, TIM4_CH2, TIM17_CH1N, TSC_G5_IO4, EVENTOUT	-
A7	94	60	44	BOOT0	I	B	-	Boot memory selection	

Table 16. Alternate functions for port C

Port & Pin Name	AF1	AF2	AF3	AF4	AF5	AF6	AF7
PC0	EVENTOUT	-	-	-	-	-	-
PC1	EVENTOUT	-	-	-	-	-	-
PC2	EVENTOUT	-	COMP7_OUT	-	-	-	-
PC3	EVENTOUT	-	-	-	-	TIM1_BKIN2	-
PC4	EVENTOUT	-	-	-	-	-	USART1_TX
PC5	EVENTOUT	-	TSC_G3_IO1	-	-	-	USART1_RX
PC6	EVENTOUT	TIM3_CH1	-		-	I2S2_MCK	COMP6_OUT
PC7	EVENTOUT	TIM3_CH2	-		-	I2S3_MCK	
PC8	EVENTOUT	TIM3_CH3	-		-	-	
PC9	EVENTOUT	TIM3_CH4	-		I2S_CKIN		-
PC10	EVENTOUT	-	-		UART4_TX	SPI3_SCK, I2S3_CK	USART3_TX
PC11	EVENTOUT	-	-		UART4_RX	SPI3_MISO, I2S3ext_SD	USART3_RX
PC12	EVENTOUT	-	-		UART5_TX	SPI3_MOSI, I2S3_SD	USART3_CK
PC13	-	-	-	TIM1_CH1N	-	-	-
PC14	-	-	-	-	-	-	-
PC15	-	-	-	-	-	-	-

2. V_{REF+} must be always lower or equal than V_{DDA} ($V_{REF+} \leq V_{DDA}$). If unused then it must be connected to V_{DDA}.
3. V_{IN} maximum must always be respected. Refer to *Table 22: Current characteristics* for the maximum allowed injected current values.
4. Include VREF- pin.

Table 22. Current characteristics

Symbol	Ratings	Max.	Unit
ΣI_{VDD}	Total current into sum of all V_{DD} power lines (source)	160	mA
ΣI_{VSS}	Total current out of sum of all V_{SS} ground lines (sink)	–160	
I_{VDD}	Maximum current into each V_{DD} power line (source)(1)	100	
I_{VSS}	Maximum current out of each V_{SS} ground line (sink)(1)	–100	
$I_{IO(PIN)}$	Output current sunk by any I/O and control pin	25	
	Output current source by any I/O and control pin	–25	
$\Sigma I_{IO(PIN)}$	Total output current sunk by sum of all IOs and control pins(2)	80	
	Total output current sourced by sum of all IOs and control pins(2)	–80	
$I_{INJ(PIN)}$	Injected current on FT, FTf and B pins(3)	-5/+0	
	Injected current on TC and RST pin(4)	± 5	
	Injected current on TTa pins(5)	± 5	
$\Sigma I_{INJ(PIN)}$	Total injected current (sum of all I/O and control pins)(6)	± 25	

1. All main power (V_{DD}, V_{DDA}) and ground (V_{SS} and V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
2. This current consumption must be correctly distributed over all I/Os and control pins.The total output current must not be sunk/sourced between two consecutive power supply pins referring to high pin count LQFP packages.
3. Positive injection is not possible on these I/Os and does not occur for input voltages lower than the specified maximum value.
4. A positive injection is induced by $V_{IN} > V_{DD}$ while a negative injection is induced by $V_{IN} < V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to *Table 21: Voltage characteristics* for the maximum allowed input voltage values.
5. A positive injection is induced by $V_{IN} > V_{DDA}$ while a negative injection is induced by $V_{IN} < V_{SS}$. I_{INJ}(PIN) must never be exceeded. Refer to *Table 21: Voltage characteristics* for the maximum allowed input voltage values. Negative injection disturbs the analog performance of the device. See note (2) below *Table 70*.
6. When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values).

Table 23. Thermal characteristics

Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	–65 to +150	°C
T_J	Maximum junction temperature	150	°C

Table 36. Typical current consumption in Sleep mode, code running from Flash or RAM

Symbol	Parameter	Conditions	f_{HCLK}	Typ		Unit
				Peripherals enabled	Peripherals disabled	
I_{DD}	Supply current in Sleep mode from V_{DD} supply	Running from HSE crystal clock 8 MHz, code executing from Flash or RAM	72 MHz	44.1	7.0	mA
			64 MHz	39.7	6.3	
			48 MHz	30.3	4.9	
			32 MHz	20.5	3.5	
			24 MHz	15.4	2.8	
			16 MHz	10.6	2.0	
			8 MHz	5.4	1.1	
			4 MHz	3.2	1.0	
			2 MHz	2.1	0.9	
			1 MHz	1.5	0.8	
			500 kHz	1.2	0.8	
			125 kHz	1.0	0.8	
I_{DDA} (1) (2)	Supply current in Sleep mode from V_{DDA} supply		72 MHz	239.7	238.5	µA
			64 MHz	210.5	209.6	
			48 MHz	155.0	155.6	
			32 MHz	105.3	105.2	
			24 MHz	81.9	81.8	
			16 MHz	58.7	58.6	
			8 MHz	2.4	2.4	
			4 MHz	2.4	2.4	
			2 MHz	2.4	2.4	
			1 MHz	2.4	2.4	
			500 kHz	2.4	2.4	
			125 kHz	2.4	2.4	

1. V_{DDA} monitoring is ON.
2. When peripherals are enabled, the power consumption of the analog part of peripherals such as ADC, DAC, Comparators, OpAmp etc. is not included. Refer to the tables of characteristics in the subsequent sections.

I/O system current consumption

The current consumption of the I/O system has two components: static and dynamic.

I/O static current consumption

All the I/Os used as inputs with pull-up generate current consumption when the pin is externally held low. The value of this current consumption can be simply computed by using the pull-up/pull-down resistors values given in *Table 54: I/O static characteristics*.

For the output pins, any external pull-down or external load must also be considered to estimate the current consumption.

Additional I/O current consumption is due to I/Os configured as inputs if an intermediate voltage level is externally applied. This current consumption is caused by the input Schmitt trigger circuits used to discriminate the input value. Unless this specific configuration is required by the application, this supply current consumption can be avoided by configuring these I/Os in analog mode. This is notably the case of ADC input pins which should be configured as analog inputs.

Caution: Any floating input pin can also settle to an intermediate voltage level or switch inadvertently, as a result of external electromagnetic noise. To avoid current consumption related to floating pins, they must either be configured in analog mode, or forced internally to a definite digital value. This can be done either by using pull-up/down resistors or by configuring the pins in output mode.

I/O dynamic current consumption

In addition to the internal peripheral current consumption (see *Table 38: Peripheral current consumption*), the I/Os used by an application also contribute to the current consumption. When an I/O pin switches, it uses the current from the MCU supply voltage to supply the I/O pin circuitry and to charge/discharge the capacitive load (internal or external) connected to the pin:

$$I_{SW} = V_{DD} \times f_{SW} \times C$$

where

I_{SW} is the current sunk by a switching I/O to charge/discharge the capacitive load

V_{DD} is the MCU supply voltage

f_{SW} is the I/O switching frequency

C is the total capacitance seen by the I/O pin: $C = C_{INT} + C_{EXT} + C_S$

The test pin is configured in push-pull output mode and is toggled by software at a fixed frequency.

On-chip peripheral current consumption

The MCU is placed under the following conditions:

- all I/O pins are in analog input configuration
- all peripherals are disabled unless otherwise mentioned
- the given value is calculated by measuring the current consumption
  - with all peripherals clocked off
  - with only one peripheral clocked on
- ambient operating temperature at 25°C and $V_{DD} = V_{DDA} = 3.3$ V.

Table 38. Peripheral current consumption

Peripheral	Typical consumption(1)	Unit
	I_{DD}	
BusMatrix (2)	12.6	µA/MHz
DMA1	7.6	
DMA2	6.1	
CRC	2.1	
GPIOA	10.0	
GPIOB	10.3	
GPIOC	2.2	
GPIOD	8.8	
GPIOE	3.3	
GPIOF	3.0	
TSC	5.5	
ADC1&2	17.3	
APB2-Bridge (3)	3.6	
SYSCFG	7.3	
TIM1	40.0	
SPI1	8.8	
USART1	23.3	
TIM15	17.1	
TIM16	10.1	
TIM17	11.0	
APB1-Bridge (3)	6.1	
TIM2	49.1	
TIM3	38.8	
TIM4	38.3	

6.3.11 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB**: A Burst of Fast Transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in *Table 49*. They are based on the EMS levels and classes defined in the application note AN1709.

Table 49. EMS characteristics

Symbol	Parameter	Conditions	Level/ Class
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V_{DD} = 3.3 V, LQFP100, T_A = +25°C, f_{HCLK} = 72 MHz conforms to IEC 61000-4-2	3B
V_{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	V_{DD} = 3.3 V, LQFP100, T_A = +25°C, f_{HCLK} = 72 MHz conforms to IEC 61000-4-4	4A

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (control registers...)

6.3.14 I/O port characteristics

General input/output characteristics

Unless otherwise specified, the parameters given in *Table 54* are derived from tests performed under the conditions summarized in *Table 24*. All I/Os are CMOS and TTL compliant.

Table 54. I/O static characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IL}	Low level input voltage	TC and TTa I/O	-	-	$0.3\ V_{DD}+0.07$ (1)	V
		FT and FTf I/O	-	-	$0.475\ V_{DD}-0.2$ (1)	
		BOOT0	-	-	$0.3\ V_{DD}–0.3$ (1)	
		All I/Os except BOOT0	-	-	$0.3\ V_{DD}$ (2)	
V_{IH}	High level input voltage	TC and TTa I/O	$0.445\ V_{DD}+0.398$ (1)	-	-	
		FT and FTf I/O	$0.5\ V_{DD}+0.2$ (1)	-	-	
		BOOT0	$0.2\ V_{DD}+0.95$ (1)	-	-	
		All I/Os except BOOT0	$0.7\ V_{DD}$ (2)	-	-	
V_{hys}	Schmitt trigger hysteresis	TC and TTa I/O	-	200 (1)	-	mV
		FT and FTf I/O	-	100 (1)	-	
		BOOT0	-	300 (1)	-	
I_{lkg}	Input leakage current (3)	TC, FT and FTf I/O TTa I/O in digital mode $V_{SS} \le V_{IN} \le V_{DD}$	-	-	±0.1	µA
		TTa I/O in digital mode $V_{DD} \le V_{IN} \le V_{DDA}$	-	-	1	
		TTa I/O in analog mode $V_{SS} \le V_{IN} \le V_{DDA}$	-	-	±0.2	
		FT and FTf I/O(4) $V_{DD} \le V_{IN} \le 5$ V	-	-	10	
R_{PU}	Weak pull-up equivalent resistor(5)	$V_{IN} = V_{SS}$	25	40	55	kΩ
R_{PD}	Weak pull-down equivalent resistor(5)	$V_{IN} = V_{DD}$	25	40	55	kΩ
C_{IO}	I/O pin capacitance	-	-	5	-	pF

1. Data based on design simulation.
2. Tested in production.
3. Leakage could be higher than the maximum value. if negative current is injected on adjacent pins. Refer to *Table 53: I/O current injection susceptibility*.
4. To sustain a voltage higher than V_{DD} +0.3 V, the internal pull-up/pull-down resistors must be disabled.
5. Pull-up and pull-down resistors are designed with a true resistance in series with a switchable PMOS/NMOS. This PMOS/NMOS contribution to the series resistance is minimum (~10% order).

Table 59. IWDG min/max timeout period at 40 kHz (LSI) (1)

Prescaler divider	PR[2:0] bits	Min timeout (ms) RL[11:0]= 0x000	Max timeout (ms) RL[11:0]= 0xFFF
/4	0	0.1	409.6
/8	1	0.2	819.2
/16	2	0.4	1638.4
/32	3	0.8	3276.8
/64	4	1.6	6553.6
/128	5	3.2	13107.2
/256	7	6.4	26214.4

1. These timings are given for a 40 kHz clock but the microcontroller's internal RC frequency can vary from 30 to 60 kHz. Moreover, given an exact RC oscillator frequency, the exact timings still depend on the phasing of the APB interface clock versus the LSI clock so that there is always a full RC period of uncertainty.

Table 60. WWDG min-max timeout value @72 MHz (PCLK)(1)

Prescaler	WDGTB	Min timeout value	Max timeout value
1	0	0.05687	3.6409
2	1	0.1137	7.2817
4	2	0.2275	14.564
8	3	0.4551	29.127

1. Guaranteed by design.

SPI/I^2S characteristics

Unless otherwise specified, the parameters given in *Table 63* for SPI or in *Table 64* for I^2S are derived from tests performed under ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in *Table 24*.

Refer to *Section 6.3.14: I/O port characteristics* for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO for SPI and WS, CK, SD for I^2S).

Table 63. SPI characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{SCK} $1/t_{c(SCK)}$	SPI clock frequency	Master mode, SPI1 $2.7<V_{DD}<3.6$	-	-	24	MHz
		Slave mode, SPI1 $2.7<V_{DD}<3.6$			24	
		Master mode, SPI1/2/3 $2<V_{DD}<3.6$			18	
		Slave mode, SPI1/2/3 $2<V_{DD}<3.6$			18	
DuCy(SCK)	Duty cycle of SPI clock frequency	Slave mode	30	50	70	%
$t_{su(NSS)}$	NSS setup time	Slave mode, SPI presc = 2	4*Tpclk	-	-	ns
$t_{h(NSS)}$	NSS hold time	Slave mode, SPI presc = 2	2*Tpclk	-	-	
$t_{w(SCKH)}$ $t_{w(SCKL)}$	SCK high and low time	Master mode	Tpclk-2	Tpclk	Tpclk+2	
$t_{su(MI)}$	Data input setup time	Master mode	5.5	-	-	
$t_{su(SI)}$		Slave mode	6.5	-	-	
$t_{h(MI)}$	Data input hold time	Master mode	5	-	-	
$t_{h(SI)}$		Slave mode	5	-	-	
$t_{a(SO)}$	Data output access time	Slave mode	0	-	4*Tpclk	
$t_{dis(SO)}$	Data output disable time	Slave mode	0	-	24	
$t_{v(SO)}$	Data output valid time	Slave mode	-	12	27	
		Slave mode, SPI1 $2.7<V_{DD}<3.6V$	-	12	18	
$t_{v(MO)}$		Master mode	-	1.5	3	
$t_{h(SO)}$	Data output hold time	Slave mode	11	-	-	
$t_{h(MO)}$		Master mode	0	-	-	

1. Guaranteed by characterization results.

USB characteristics

Table 65. USB startup time

Symbol	Parameter	Max	Unit
$t_{STARTUP}$(1)	USB transceiver startup time	1	µs

1. Guaranteed by design.

Table 66. USB DC electrical characteristics

Symbol	Parameter	Conditions	Min.(1)	Max.(1)	Unit
Input levels					
V_{DD}	USB operating voltage(2)	-	3.0(3)	3.6	V
V_{DI}(4)	Differential input sensitivity	I(USB_DP, USB_DM)	0.2	-	V
V_{CM}(4)	Differential common mode range	Includes V_{DI} range	0.8	2.5	
V_{SE}(4)	Single ended receiver threshold	-	1.3	2.0	
Output levels					
V_{OL}	Static output level low	R_L of 1.5 kΩ to 3.6 V(5)	-	0.3	V
V_{OH}	Static output level high	R_L of 15 kΩ to V_{SS}(5)	2.8	3.6	

1. All the voltages are measured from the local ground potential.
2. To be compliant with the USB 2.0 full-speed electrical specification, the USB_DP (D+) pin should be pulled up with a 1.5 kΩ resistor to a 3.0-to-3.6 V voltage range.
3. The STM32F302xB/STM32F302xC USB functionality is ensured down to 2.7 V but not the full USB electrical characteristics which are degraded in the 2.7-to-3.0 V V_{DD} voltage range.
4. Guaranteed by design.
5. R_L is the load connected on the USB drivers.

Figure 31. USB timings: definition of data signal rise and fall time

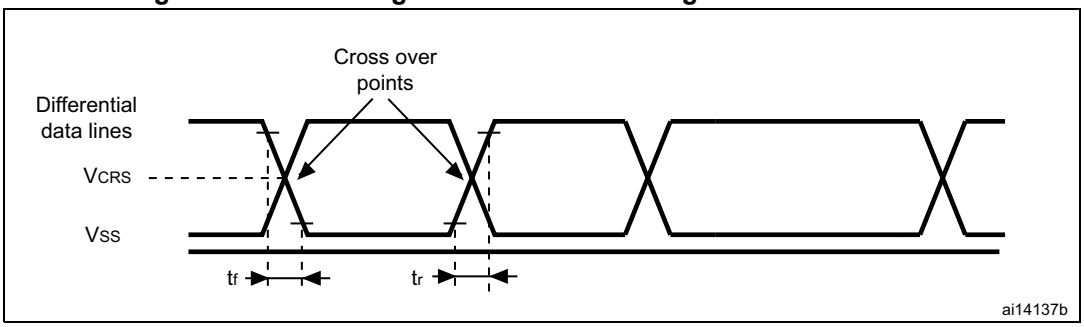


Figure 32. ADC typical current consumption on VDDA pin

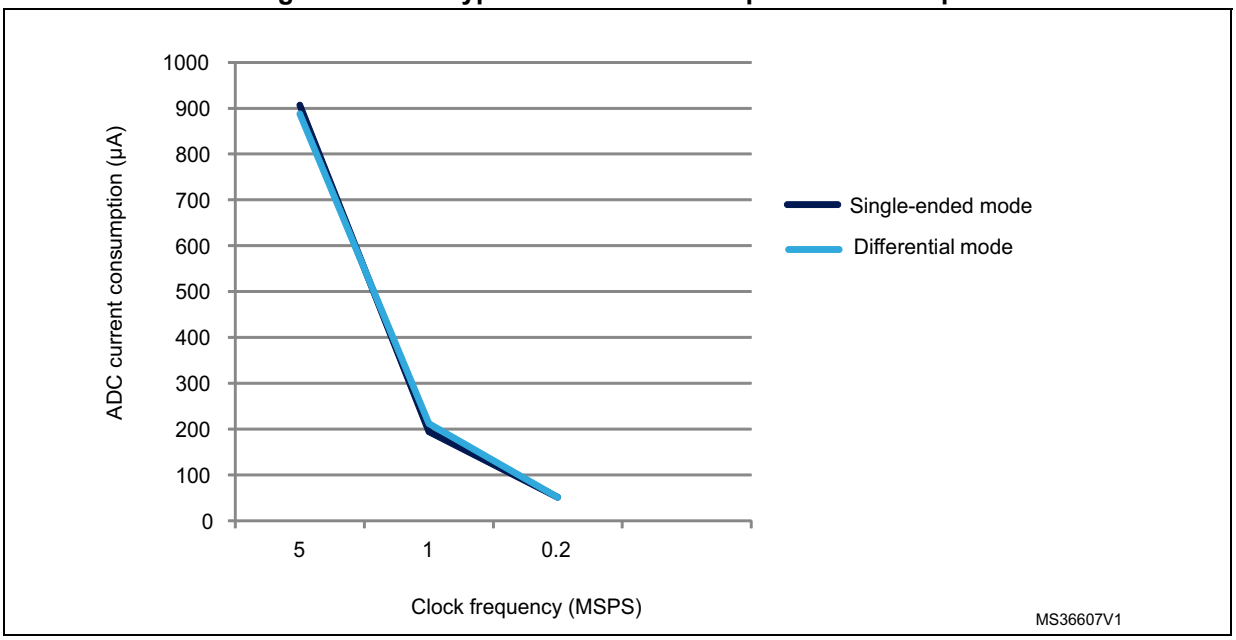


Figure 33. ADC typical current consumption on VREF+ pin

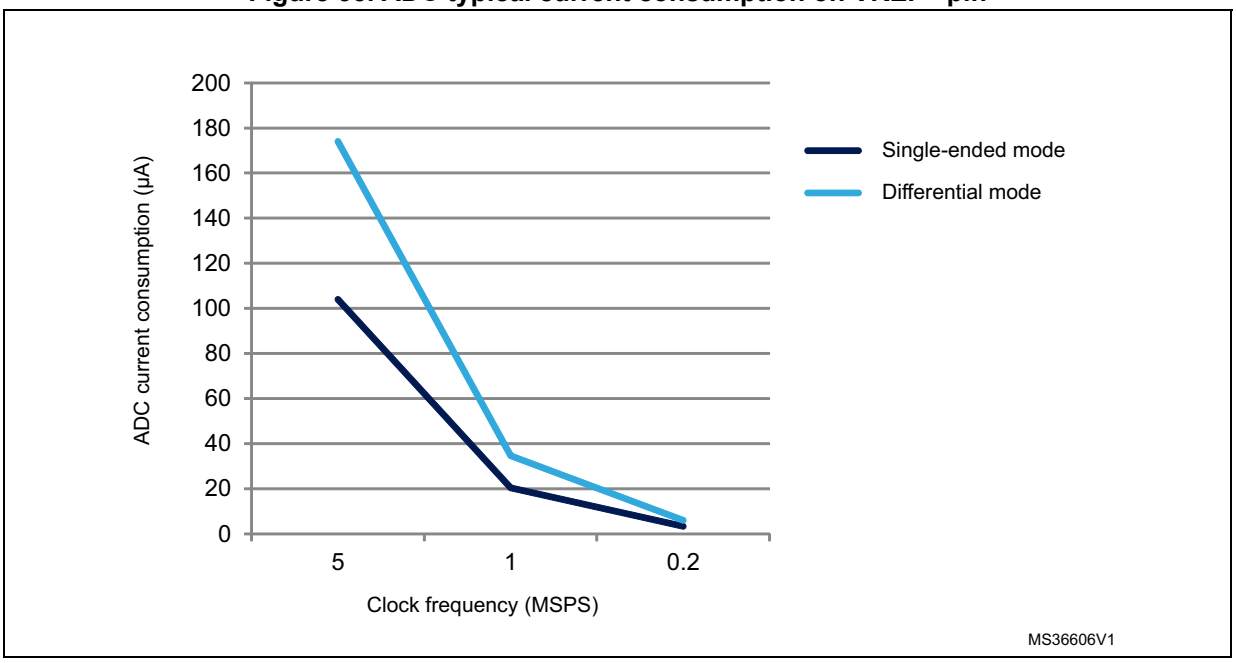


Table 73. ADC accuracy, 64-pin packages(1)(2)(3) (continued)

Symbol	Parameter	Conditions			Min(4)	Max (4)	Unit
SNR(5)	Signal-to-noise ratio	ADC clock freq. ≤ 72 MHz, Sampling freq ≤ 5 Msps, 2 V ≤ V_{DDA} ≤ 3.6 V 64-pin package	Single ended	Fast channel 5.1 Ms	64	-	dB
				Slow channel 4.8 Ms	64	-	
			Differential	Fast channel 5.1 Ms	67	-	
				Slow channel 4.8 Ms	67	-	
THD(5)	Total harmonic distortion		Single ended	Fast channel 5.1 Ms	-	-75	
				Slow channel 4.8 Ms	-	-75	
			Differential	Fast channel 5.1 Ms	-	-79	
				Slow channel 4.8 Ms	-	-78	

1. ADC DC accuracy values are measured after internal calibration.
2. ADC accuracy vs. negative Injection Current: Injecting negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative current.
Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in *Section 6.3.14* does not affect the ADC accuracy.
3. Better performance may be achieved in restricted V_{DDA}, frequency and temperature ranges.
4. Guaranteed by characterization results.
5. Value measured with a -0.5 dB full scale 50 kHz sine wave input signal.

Table 74. ADC accuracy at 1MSPS(1)(2)

Symbol	Parameter	Test conditions		Typ	Max(3)	Unit
ET	Total unadjusted error	ADC Freq ≤ 72 MHz Sampling Freq ≤ 1MSPS 2.4 V ≤ V_{DDA} = V_{REF+} ≤ 3.6 V Single-ended mode	Fast channel	±2.5	±5	LSB
			Slow channel	±3.5	±5	
EO	Offset error		Fast channel	±1	±2.5	
			Slow channel	±1.5	±2.5	
EG	Gain error		Fast channel	±2	±3	
			Slow channel	±3	±4	
ED	Differential linearity error		Fast channel	±0.7	±2	
			Slow channel	±0.7	±2	
EL	Integral linearity error		Fast channel	±1	±3	
			Slow channel	±1.2	±3	

1. ADC DC accuracy values are measured after internal calibration.
2. ADC accuracy vs. negative Injection Current: Injecting negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative current.. Any positive injection current within the limits specified for IINJ(PIN) and ∑IINJ(PIN) in *Section 6.3.14: I/O port characteristics* does not affect the ADC accuracy.
3. Guaranteed by characterization results.

6.3.23 V_{BAT} monitoring characteristics

Table 80. V_{BAT} monitoring characteristics

Symbol	Parameter	Min	Typ	Max	Unit
R	Resistor bridge for V_{BAT}	-	50	-	KΩ
Q	Ratio on V_{BAT} measurement	-	2	-	
Er(1)	Error on Q	-1	-	+1	%
T_{S_vbat}(1)(2)	ADC sampling time when reading the V_{BAT} 1mV accuracy	2.2	-	-	µs

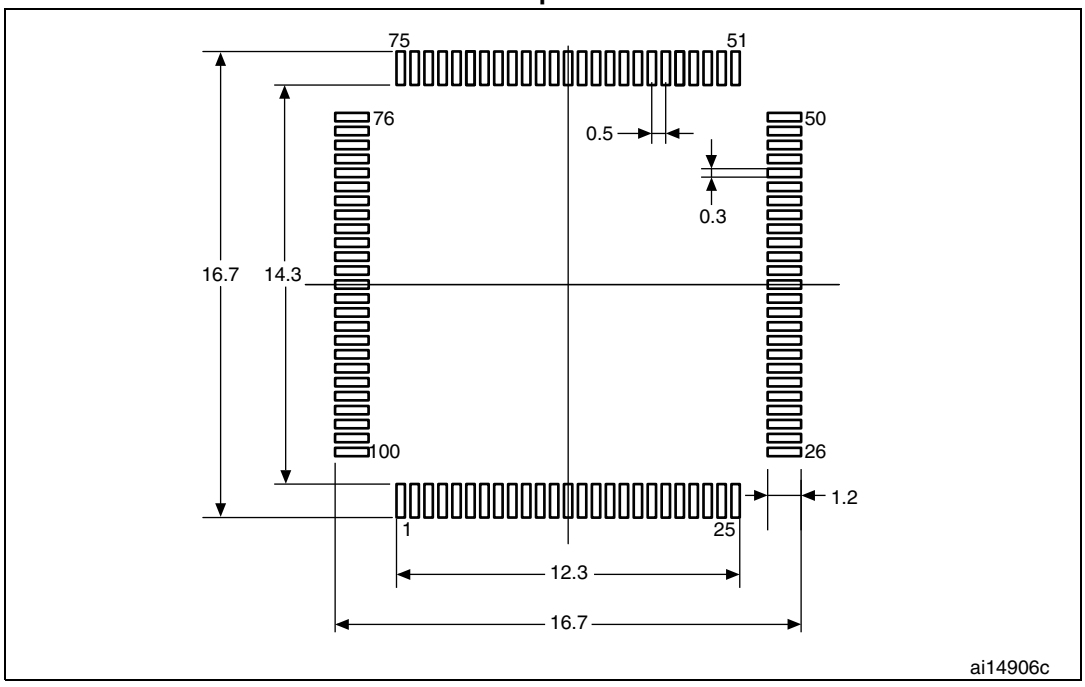
1. Guaranteed by design.
2. Shortest sampling time can be determined in the application by multiple iterations.

Table 81. LQPF100 – 14 x 14 mm, low-profile quad flat package mechanical data (continued)

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A2	1.35	1.40	1.45	0.0531	0.0551	0.0571
b	0.17	0.22	0.27	0.0067	0.0087	0.0106
c	0.09	-	0.2	0.0035	-	0.0079
D	15.80	16.00	16.2	0.622	0.6299	0.6378
D1	13.80	14.00	14.2	0.5433	0.5512	0.5591
D3	-	12.00	-	-	0.4724	-
E	15.80	16.00	16.2	0.622	0.6299	0.6378
E1	13.80	14.00	14.2	0.5433	0.5512	0.5591
E3	-	12.00	-	-	0.4724	-
e	-	0.50	-	-	0.0197	-
L	0.45	0.60	0.75	0.0177	0.0236	0.0295
L1	-	1.00	-	-	0.0394	-
K	0°	3.5°	7°	0°	3.5°	7°
ccc	-	-	0.08	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 40. LQFP100 – 14 x 14 mm, low-profile quad flat package recommended footprint



1. Dimensions are in millimeters.

Table 84. WLCSP100 – 100L, 4.166 x 4.628 mm 0.4 mm pitch wafer level chip scale package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Typ	Min	Max
A	0.525	0.555	0.585	0.0207	0.0219	0.0230
A1	-	0.17	-	-	0.0067	-
A2	-	0.38	-	-	0.0150	-
A3[2]	-	0.025	-	-	0.0010	-
Ø b[3]	0.22	0.25	0.28	-	0.0098	0.0110
D	4.166	4.201	4.236	-	0.1654	0.1668
E	4.628	4.663	4.698	-	0.1836	0.1850
e	-	0.4	-	-	0.0157	-
e1	-	3.6	-	-	0.1417	-
e2	-	3.6	-	-	0.1417	-
F	-	0.3005	-	-	0.0118	-
G	-	0.5315	-	-	0.0209	-
N	-	100	-	-	3.9370	-
aaa	-	0.1	-	-	0.0039	-
bbb	-	0.1	-	-	0.0039	-
ccc	-	0.1	-	-	0.0039	-
ddd	-	0.05	-	-	0.0020	-
eee	-	0.05	-	-	0.0020	-

1. Values in inches are converted from mm and rounded to 4 decimal digits.
2. Back side coating.
3. Dimension is measured at the maximum bump diameter parallel to primary datum Z.